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10/586,507	07/17/2006	Clemens Gerhardus Johannes De Haas	NL04 0061 US1	4614
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NXP, B.V.			HILTUNEN, THOMAS J	
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SAN JOSE, CA 95131				
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			07/30/2008	ELECTRONIC

**Please find below and/or attached an Office communication concerning this application or proceeding.**

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

ip.department.us@nxp.com

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>
	10/586,507	DE HAAS, CLEMENS GERHARDUS JOHANNES
<b>Examiner</b>	<b>Art Unit</b>	
Thomas J. Hiltunen	2816	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

- 1) Responsive to communication(s) filed on 12 May 2008.  
 2a) This action is **FINAL**.                    2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

- 4) Claim(s) 1-9 is/are pending in the application.  
 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
 5) Claim(s) 6 and 7 is/are allowed.  
 6) Claim(s) 1-3,8 and 9 is/are rejected.  
 7) Claim(s) 4 and 5 is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

- 9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on 12 May 2008 is/are: a) accepted or b) objected to by the Examiner.  
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

- |  |   |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)          | 4) <input type="checkbox"/> Interview Summary (PTO-413)           |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ .                                    |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08)          | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date _____.   | 6) <input type="checkbox"/> Other: _____ .                        |

## **DETAILED ACTION**

Applicant's amendment filed 12 May 2008 has been received and entered in the case. Claims 1-3, 8 and 9 are rejected as necessitated by amendment.

### ***Drawings***

The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the "source-drain diodes in anti-series" coupled to the first and second MOS transistors/PMOS and NMOS pairs as recited in claims 1 and 8 must be shown or the feature(s) canceled from the claim(s). No new matter should be entered.

Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner,

the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

***Claim Rejections - 35 USC § 102***

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-3, 8 and 9 are rejected under 35 U.S.C. 102(b) as being anticipated by Ausserlechner et al. (USPN 6,559,721).

With respect to claim 1, Ausserlechner et al. discloses in Figs. 2 and 10, an electronic circuit, comprising a signal conductor (OUT), a power supply reference conductor (VDD) and a switching circuit (P1 and N1) coupled between the signal conductor (OUT) and the power supply reference conductor (VDD), the switching circuit comprising:

a substrate arrangement (nSUB and Sn, see Fig. 4) coupled to the power supply reference conductor (nSUB is connected to VDD, see Col. 7 lines 34-37);

a first MOS transistor (P1) realized on said substrate arrangement (Sn, see Fig. 4) with a source, a drain and a gate, the source being coupled to the power supply reference conductor (VDD), the first MOS transistor (P1) having a first conductivity type (PMOS);

a second MOS transistor (N1) realized on said substrate arrangement (Sn, see Fig. 4) with a source, a drain and a gate, the source being coupled to the drain of the first MOS transistor (when the transistors P1 and N1 become conductive, i.e., are turned on, then their respective source and drains will be connected together through the source to drain conduction paths of each transistor device. Furthermore, in CMOS technology there is no structural difference between the drain and source of a MOS transistor, thus a source of a transistor is the same as a drain of a transistor), the drain being coupled to the signal conductor (the drain of N1 is connected to OUT), the second MOS transistor (N1) having a second conductivity type opposite the first conductivity type (NMOS);

a control circuit (PA, CP1, CP2) with outputs coupled to the gate of the first MOS transistor (A1 coupled to G1) and the gate and source of the second MOS transistor (output of CP1 to G2, CP1 is coupled to the source of N1, since CP1 is coupled to the Vdd terminal, which is coupled to the source of N1 via P1. Thus CP1 is coupled to the source and gate of N1), the control circuit being arranged to switch between an "on" state and an "off" state, in which the control circuit controls the gate source voltages of the first and second MOS transistor to make channels of these MOS transistors conductive and not to make the channels of these first and second transistors conductive respectively (the control circuit signals output to the gates of P1 and N1 control the gate source voltages of P1 and N1 thus turning P1 and N1 on and off).

wherein each of the first and second MOS transistors have source-drain diodes in anti-series (D2 which is coupled to the source and drain of P1 and D3 which is

coupled to the source and drain of N1) so that said first and second MOS transistors have a respective maximum breakdown voltage at drain voltages in mutually opposite directions relative to a substrate (D2 and D3 are connected as recited. Thus, D2 and D3 operate to control the breakdown voltage of P1 and N1 as recited. Furthermore, P1 and N1 are complementary transistors thus they have breakdown voltages in mutually opposite directions).

With respect to claim 2, Ausserlechner et al. discloses, an electronic circuit according to claim 1, comprising a further power supply reference conductor (GND) and a further switching circuit (N2 and P2), complementary to the switching circuit, the further switching circuit comprising:

a third MOS transistor (N2) of the second conductivity type (NMOS), having a source, a drain and a gate, the source being coupled to the further power supply reference conductor (GND);

a second MOS transistor (P2) of the first conductivity type (PMOS), with a source, a drain and a gate, the source being coupled to the drain of the third MOS transistor (when the transistors P2 and N2 become conductive, i.e., are turned on, then their respective source and drains will be connected together through the source to drain conduction paths of each transistor device. Furthermore, in CMOS technology there is no structural difference between the drain and source of a MOS transistor, thus a source of a transistor is the same as a drain of a transistor), the drain being coupled to the signal conductor (OUT) or a further signal conductor;

the control circuit (PA and CP2) having outputs coupled to the gate of the third MOS transistor (A2 coupled to G4 of N2) and the gate and source of the fourth MOS transistor (CP2 is coupled to the gate of P2, i.e., G3, and the source of P2 through N2, since CP2 is coupled to GND wherein the source of P2 is coupled to GND through N2. Thus, CP2 is coupled to the source of P2 via N2), the control circuit applying gate source voltages to the third and fourth MOS transistor to make these third and fourth MOS transistors conductive and not to make these transistors conductive respectively (the control circuit signals output to the gates of P1 and N1 control the gate source voltages of P1 and N1 thus turning P1 and N1 on and off).

With respect to claim 3, Ausserlechner et al. discloses, an electronic circuit according to claim 2, wherein the control circuit (PA, CP1 and CP2) is arranged to supply first substantially matching gate-source voltages to the first and fourth MOS transistor and second substantially matching gate-source voltages to the second and third MOS transistor (PA outputs symmetrical voltages A1 and A2. Similarly, CP1 and CP2 output two symmetrical signals that are shifted 3 Volts above VDD and below GND, respectively. Thus, the gate to source voltages of P1 and P2 will be substantially the same with respect to logic value, i.e., both transistors will be activated by low voltages, and the of the gate to source voltages of N1 and P2 will have substantially the same logic level, i.e., both will be activated by high voltage levels. Furthermore, there is no explicitly recited definition of "substantially matching" within the claims. Thus, the 3 Volt offset at the output of CP1 and CP2 is "substantially matching" in that both P1 and P2 are active low and N1 and N2 are active high).

With respect to claim 8, Ausserlechner et al. discloses in Fig. 2 and 4, an electronic circuit, comprising a signal conductor (OUT), a first and second power supply conductor (VDD, GND), a first switching circuit coupled between the first power supply conductor and the signal conductor (P1 and N1) and a second switching circuit coupled between the second power supply conductor and the signal conductor (N2 and P2) or a further signal conductor (202), the first switching circuit comprising:

a first PMOS transistor (P1) with a source, a drain and a gate, the source being coupled to the first power supply conductor (VDD);

a first NMOS transistor (N1) with a source, a drain and a gate, the source being coupled to the drain of the first PMOS transistor (when the transistors P1 and N1 become conductive, i.e., are turned on, then their respective source and drains will be connected together through the source to drain conduction paths of each transistor device. Furthermore, in CMOS technology there is no structural difference between the drain and source of a MOS transistor, thus a source of a transistor is the same as a drain of a transistor), the drain being coupled to the signal conductor (the drain of N1 is connected to OUT), the drain being coupled to the signal conductor (OUT);

the second switching circuit comprising:

a second NMOS transistor (N2) with a source, a drain and a gate, the source being coupled to the second power supply conductor (GND);

a second PMOS transistor (P2) with a source, a drain and a gate, the source being coupled to the drain of the second NMOS transistor (when the transistors P2 and N2 become conductive, i.e., are turned on, then their respective source and drains will

be connected together through the source to drain conduction paths of each transistor device. Furthermore, in CMOS technology there is no structural difference between the drain and source of a MOS transistor, thus a source of a transistor is the same as a drain of a transistor), the drain being coupled to the signal conductor (the drain of N1 is connected to OUT), the drain being coupled to the signal conductor (OUT) or the further signal conductor (202); the electronic circuit comprising:

a control circuit (PA, CP1, and CP2) with outputs coupled to the gate of the first PMOS transistor (A1 coupled to G1), the gate of the second NMOS transistor (A2 coupled to G4), the gate and source of the first NMOS transistor (output of CP1 coupled to the gate of N1, CP1 is coupled to the source of N1, since CP1 is coupled to VDD and the source of N1 is coupled to VDD via P1) and the gate and source of the second PMOS transistor (CP2 coupled to the gate of P2, CP2 is coupled to the source of P2, since CP2 is coupled GND and the source of P2 is coupled to ground via N2), the control circuit being arranged to switch between an "on" state and an "off" state, in which the control circuit controls the second NMOS transistor to make channels of these transistors conductive and not to make the channels of these first and second transistors conductive respectively (the control signals output to the gates of P1, N1, P2 and N2 control the gate source voltages of each respective transistor to turn each transistor on and off).

wherein each pair of PMOS and NMOS transistors have source-drain diodes in anti-series (D2 and D4 are coupled to the source and drain of P1 and P2 and D3 and D6 are coupled to the source and drain of N1 and N2) so that said each pair of PMOS

and NMOS transistors have a respective maximum breakdown voltage at drain voltages in mutually opposite directions relative to a substrate voltage (D2 with D4 and D3 with D6 are connected as recited. Thus, D2, D3, D4 and D6 operate to control the breakdown voltage of P1, P2, N1 and N2 as recited. Furthermore, P1, P2, N1 and N2 are complementary transistors thus they have breakdown voltages in mutually opposite directions).

With respect to claim 9, Ausserlechner et al. discloses, an electronic circuit according to claim 8, wherein the control circuit is arranged to supply first substantially matching gate-source voltages to the first and second PMOS transistor and second substantially matching gate-source voltages to the first and second NMOS transistor (PA outputs symmetrical voltages A1 and A2. Similarly, CP1 and CP2 output two symmetrical signals shifted 3 Volts above VDD and below GND, respectively. Thus, the gate to source voltages of P1 and P2 will be substantially the same with respect to logic value, i.e., both will be activated by low voltages, and the of the gate to source voltages of N1 and P2 will have substantially the same logic level, i.e., both will be activated by high voltage levels. Furthermore, there is no explicitly recited definition of "substantially matching" within the claims. Thus, the 3 Volt offset at the output of CP1 and CP2 is "substantially matching" in that both P1 and P2 are active low and N1 and N2 are active high).

***Allowable Subject Matter***

Claims 4 and 5 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

With respect to claims 4, there is no cited art that discloses a control circuit to operate the first MOS to become conductive by supplying a voltage opposite the polarity of the supply voltage supplied by a pump circuit in further combination with a switch circuit having a first and second MOS transistor, wherein the source and gate of the second MOS transistor is coupled to the control circuit and the first and second MOS transistors have antiparallel source-drain diodes to control the MOS transistors to have maximum breakdown voltages in mutually opposite directions as recited in claim 1.

With respect to claim 5, there is no cited art that discloses a control circuit to operate the first MOS to become conductive by supplying a voltage opposite the polarity of the supply voltage including a resistor and current source connected to the second MOS transistor as recited in further combination with a switch circuit having a first and second MOS transistor, wherein the source and gate of the second MOS transistor is coupled to the control circuit and the first and second MOS transistors have antiparallel source-drain diodes to control the MOS transistors to have maximum breakdown voltages in mutually opposite directions as recited in claim 1.

Claims 6 and 7 are allowed.

With respect to claim 6, there is no cited art that discloses a second resistor element and a current mirror connected as recited and being connected to the resistive

element, the power supply reference conductor, the further power supply reference conductor and second MOS transistor of the circuit as recited in 6. Claim 7 is allowable for at least the same reasons as claim 6.

### ***Cited Art***

Imaizumi (USPN 6,018,252) discloses a switching circuit (62 with 72) having a first transistor connected to a pump circuit wherein the first and second MOS transistor are connected as recited, except the source and gate of 62 are not connected to a control circuit.

Tomari et al. (USPAPN 2004/0095182) discloses in Fig. 2 a switching circuit (N11 and P11) connected as recited in claim 1, except the source and gate of “the second transistor” are not connected to a control circuit.

### ***Response to Arguments***

Applicant's arguments filed 12 May 2008 have been fully considered but they are not persuasive.

Assuming, arguendo, that source terminal and drain terminal of a MOS transistor are in fact constructed differently in CMOS as suggested by Applicant that is not to say the source terminal and drain terminal of the MOS transistors of Ausserlechner are not “connected” as recited. For instance, when a MOS transistor turns on, i.e., becomes conductive, its source is connected to its drain to allow current to flow through its source to its drain. Thus when both P1 and N1 are on the drain of P1 is connected to the

source of N1 through the source to drain conduction path of N1. Furthermore, the drain of N1 is connected to the OUT terminal when N1 is conductive. The recitation of "connected" does not require a direct connection but rather a connection which may include additional elements between the recited source and drains. Thus Ausserlechner discloses all the limitations of claim 1.

***Conclusion***

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thomas J. Hiltunen whose telephone number is (571)272-5525. The examiner can normally be reached on M-F 8:00am - 4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lincoln Donovan can be reached on (571)272-1988. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

**TH**  
**July 23, 2008**  
/Lincoln Donovan/  
Supervisory Patent Examiner, Art Unit 2816